

TECHNICAL DATA, PROVISIONAL DATA ONLY DATA SHEET 4984, REV. B

# HERMETIC SILICON CARBIDE RECTIFIER

**DESCRIPTION**: A 1200-VOLT, 40 AMP POWER SILICON CARBIDE RECTIFIER IN A HERMETIC TO-258 PACKAGE WITH CERAMIC SEAL

#### **FEATURES:**

- NO RECOVERY TIME OR REVERSE RECOVERY LOSSES
- NO TEMPERATURE INFLUENCE ON SWITCHING BEHAVIOR
- SCREENED VERSIONS ARE AVAILABLE

### **MAXIMUM RATINGS**

ALL RATINGS ARE @ T<sub>C</sub> = 25 °C UNLESS OTHERWISE SPECIFIED.

PIV	1200	Volts
lo	20	Amps
I <sub>FRM</sub>	60	Amps
I <sub>FSM</sub>	250	Amps
P <sub>d</sub>	80	W
$R_{ heta JC}$	0.5	°C/W
Тор	-55 to +175	°C
Tstg	-55 to +200	°C
	I <sub>o</sub> I <sub>FRM</sub> I <sub>FSM</sub> P <sub>d</sub> R <sub>0</sub> JC  Top	I <sub>O</sub> 20  I <sub>FRM</sub> 60  I <sub>FSM</sub> 250  P <sub>d</sub> 80  R <sub>θJC</sub> 0.5  Top -55 to +175  Tstg -55 to

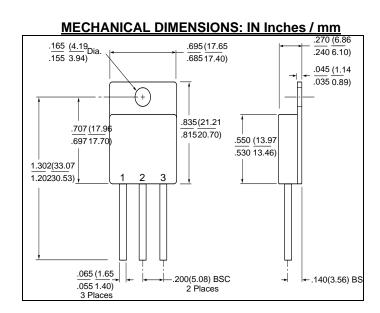
<sup>\*</sup> Note: SiC semiconductors will handle at or above this operating and storage temperature. However, extended operational use of the packaged device above 175C may reduce its future performance. All qualification testing and screening per MIL-PRF-19500 will only be performed to 175C.

# **ELECTRICAL CHARACTERISTICS**

CHARACTERISTIC		TYP	MAX.	UNITS
FORWARD VOLTAGE DROP PER LEG(I <sub>f</sub> = 20A) V <sub>f</sub>	T <sub>J</sub> = 25 °C	1.6	1.8	
	T <sub>J</sub> = 175 °C	2.5	3.0	Volts
REVERSE CURRENT PER LEG (1200V PIV) I,	T <sub>J</sub> = 25 °C	0.02	0.40	
	T <sub>J</sub> =175 °C	0.04	2.00	mA
JUNCTION CAPACITANCE (V <sub>r</sub> =400V, f = 1MHz) C <sub>T</sub> PER LEG	T <sub>J</sub> = 25 °C	140	N/A	pF
TOTAL CAPACITIVE CHARGE PER LEG ( $V_R$ =1200V $I_F$ =10A di/dt=500A/ $\mu$ s $T_J$ =25°C) $Q_C$		100	N/A	nC

## **SENSITRON**

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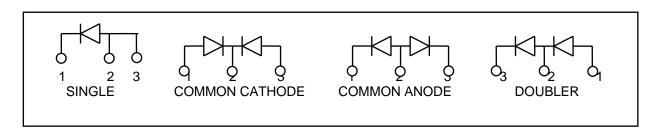


TO-258

# **PINOUT TABLE**

TYPE	PIN 1	PIN 2	PIN 3
SINGLE RECTIFIER	CATHODE	ANODE	ANODE
DUAL RECTIFIER/COMMON CATHODE (P)	ANODE 1	COMMON	ANODE 2
		CATHODE	
DUAL RECTIFIER/COMMON ANODE (N)	CATHODE 1	COMMON	CATHODE 2
		ANODE	
DUAL RECTIFIER/DOUBLER (D)	ANODE	ANODE/	CATHODE
		CATHODE	

# **SCHEMATIC**



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## TYPICAL PERFORMANCE PER LEG

Figure 1. Forward Characteristics

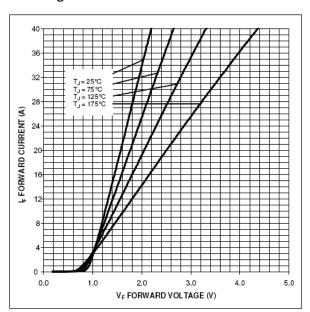
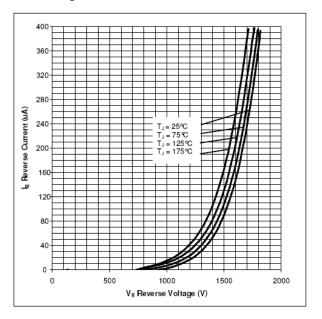


Figure 2. Reverse Characteristics



Application Note: Customers should be aware that at the current stage of technical development of SiC, the reverse avalanche capabilities of the device are limited.

Customer designs will need to accommodate these limitations and avoid exposure of the device to this and other potentially damaging conditions in their applications.

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